



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#5/A  
Jubeen  
5/23/03

In re application of : Confirmation No. 4860  
Hirotooshi KUBO : Docket No. 2001-1101  
Serial No. 09/919,797 : Group Art Unit 2822  
Filed August 2, 2001 : Examiner Jeff B Vockrodt

HIGH FREQUENCY TRANSISTOR DEVICE :

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TECHNOLOGY CENTER 2800

AMENDMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

THE COMMISSIONER IS AUTHORIZED  
TO CHARGE ANY DEFICIENCY IN THE  
FEES FOR THIS PAPER TO DEPOSIT  
ACCOUNT NO. 23-0975

Sir:

Responsive to the Office Action of November 20, 2003, a three month extension of time being filed concurrently herewith, please amend the above-identified application as follows.

In the Claims:

Kindly amend claim 1 as follows.

1. (Amended) A method of manufacturing a semiconductor device, comprising:
- forming a collector layer of a first conductivity type;
  - forming a base region of a second conductivity type formed on a top surface of said collector layer of said first conductivity type, said first conductivity type being opposite said second conductivity type, said base region being formed using epitaxial growth technology, and being formed as a single region having a uniform depth;
  - forming a groove in a top surface of said base region at a portion thereof;
  - forming spacers on sidewalls of said groove;

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